# The RF Line NPN Silicon

# High-Frequency Transistor

Designed for thick and thin-film circuits using surface mount components and requiring low-noise, high-gain signal amplification at frequencies to 1.0 GHz.

- High Gain Gpe = 17 dB Typ @ f = 450 MHz
- Low Noise NF = 2.5 dB Typ @ f = 450 MHz
- Available in tape and reel packaging options:
   T1 suffix = 3,000 units per reel

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	10	Vdc
Collector-Base Voltage	VCBO	15	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	3.0	Vdc
Collector Current — Continuous	IC	20	mAdc
Maximum Junction Temperature	T <sub>Jmax</sub>	150	°C
Power Dissipation, T <sub>case</sub> = 75°C (1) Derate linearly above T <sub>case</sub> = 75°C @	P <sub>D(max)</sub>	0.300 4.00	W mW/°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C
Thermal Resistance Junction to Case	$R_{\theta JC}$	250	°C/W

## **DEVICE MARKING**

MMBR5031LT1 = 7G

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V(BR)CEO	10	_	_	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 0.01 mAdc, I <sub>E</sub> = 0)	V(BR)CBO	15	_	_	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 0.01 mAdc, I <sub>C</sub> = 0)	V(BR)EBO	3.0	_	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 6.0 Vdc, I <sub>E</sub> = 0)	ICBO	_	_	10	nAdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 6.0 Vdc)	hFE	25	_	300	_
SMALL-SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product (I <sub>C</sub> = 5.0 mAdc, V <sub>CE</sub> = 6.0 Vdc, f = 100 MHz)	fΤ	_	1,000	_	MHz
Collector–Base Capacitance (V <sub>CE</sub> = 6.0 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz)	C <sub>cb</sub>	_	_	1.5	pF
Minimum Noise Figure (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 6.0 Vdc, f = 450 MHz)	NF <sub>min</sub>	_	2.5	_	dB
Common–Emitter Amplifier Power Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 6.0 Vdc, f = 450 MHz)	G <sub>pe</sub>	_	17	25	dB

NOTE:

# **MMBR5031LT1**

RF AMPLIFIER TRANSISTOR NPN SILICON

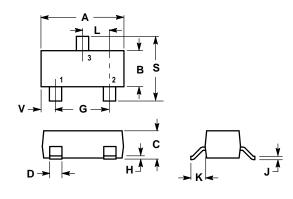


CASE 318–08, STYLE 6 SOT–23 LOW PROFILE (TO–236AA/AB)



<sup>1.</sup> Case temperature measured on collector lead immediately adjacent to body of package.

#### PACKAGE DIMENSIONS



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  MAXIUMUM LEAD THICKNESS INCLUDES

LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.1102	0.1197	2.80	3.04	
В	0.0472	0.0551	1.20	1.40	
C	0.0350	0.0440	0.89	1.11	
D	0.0150	0.0200	0.37	0.50	
G	0.0701	0.0807	1.78	2.04	
Н	0.0005	0.0040	0.013	0.100	
J	0.0034	0.0070	0.085	0.177	
K	0.0140	0.0285	0.35	0.69	
L	0.0350	0.0401	0.89	1.02	
S	0.0830	0.1039	2.10	2.64	
٧	0.0177	0.0236	0.45	0.60	

#### STYLE 6:

- PIN 1. BASE
  - EMITTER 2.
  - COLLECTOR

**CASE 318-08 ISSUE AE** 

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How to reach us:

USA/EUROPE: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298



